RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 1(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN		

Annex A: Measurement data and plots

A.1 Spectrum analyser plots: CW, 80%AM and iDEN signals



0 Hz Span CW Plot (835MHz)

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 2(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20II			N
	•	•		



0 Hz Span 80% AM Plot (835MHz)

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 3(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20II			N



0 Hz Span iDEN (835MHz)

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 4(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N



0 Hz Span CW Plot (900 MHz)

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 5(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N



0 Hz Span 80% AM Plot (900MHz)

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 6(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N



0 Hz Span iDEN (900 MHz)

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 7(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N

A.2 Dipole validation and probe modulation factor plots

Date/Time: 24/10/2008 10:08:50 AM

Test Laboratory: RTS

File Name: HAC_E_Dipole_CW835_20dBm.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 115.2 V/m; Power Drift = -0.082 dB Maximum value of Total (measured) = 147.9 V/m

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 148.3 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 115.2 V/m; Power Drift = -0.082 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in					
Grid 1	Grid 2	Grid 3			
142.2 M4	148.0 M4	146.5 M4			
Grid 4	Grid 5	Grid 6			
81.5 M4	84.0 M4	82.5 M4			
Grid 7	Grid 8	Grid 9			

Dools E field in V/

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 10(108)
Author Data	Dates of Test Report No FCC ID			
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N



 $0 \ dB = 148.3 V/m$

Date/Time: 24/10/2008 10:28:11 AM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW835_PMF_iDEN.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 123.1 V/m; Power Drift = 0.181 dB Maximum value of Total (measured) = 164.4 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 12(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	une 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 164.8 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 123.1 V/m; Power Drift = 0.181 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
156.1 M4	162.0 M4	160.2 M4
Grid 4	Grid 5	Grid 6
88.8 M4	91.9 M4	91.3 M4
Grid 7	Grid 8	Grid 9

Peak E-field in V/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 13(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	me 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN		



 $0 \ dB = 164.8 V/m$

Date/Time: 24/10/2008 10:35:27 AM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_AM80-%_835_PMF_iDEN.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: 80% AM; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 78.5 V/m; Power Drift = -0.008 dB Maximum value of Total (measured) = 100.1 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 15(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 100.6 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 78.5 V/m; Power Drift = -0.008 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	n V/m	
Grid 1	Grid 2	Grid 3
97.2 M4	100.3 M4	100.3 M4
Grid 4	Grid 5	Grid 6
55.7 M4	57.5 M4	56.8 M4
Grid 7	Grid 8	Grid 9

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RTS RIM Testing Services	Document Annex A to Hearing Aic Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ons Test CD21IN	Page 16(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N



 $0 \ dB = 100.6 V/m$

Date/Time: 24/10/2008 10:46:38 AM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_835_iDEN_PMF.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: IDEN 835; Frequency: 835 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 36.7 V/m; Power Drift = 0.001 dB Maximum value of Total (measured) = 49.4 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 18(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 49.5 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 36.7 V/m; Power Drift = 0.001 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field i	n V/m	
Grid 1	Grid 2	Grid 3
46.4 M4	48.2 M4	47.3 M4
Grid 4	Grid 5	Grid 6
26.8 M4	28.0 M4	27.4 M4
Grid 7	Grid 8	Grid 9

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 19(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N



 $0 \; dB = 49.5 V/m$

Date/Time: 24/10/2008 11:24:21 AM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW900_20dBm.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 900 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 95.7 V/m; Power Drift = 0.096 dB Maximum value of Total (measured) = 134.7 V/m

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 135.5 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 95.7 V/m; Power Drift = 0.096 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
129.8 M4	135.5 M4	134.5 M4
Grid 4	Grid 5	Grid 6
66.2 M4	68.2 M4	67.2 M4

Peak E-field in V/m

RTS RIM Testing Services	Document Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ons Test CD21IN	Page 22(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N



 $0 \; dB = 135.5 V/m$

Date/Time: 24/10/2008 11:06:25 AM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_CW900_PMF_iDEN.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 900 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 99.8 V/m; Power Drift = 0.032 dB Maximum value of Total (measured) = 136.3 V/m

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 137.6 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 99.8 V/m; Power Drift = 0.032 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Feak E-Heid III	v / 111	
Grid 1	Grid 2	Grid 3
135.6 M4	136.9 M4	133.3 M4
Grid 4	Grid 5	Grid 6
68.8 M4	72.3 M4	71.6 M4
Grid 7	Grid 8	Grid 9

Peak E-field in V/m

RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ons Test CD21IN	Page 25(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N



 $0 \ dB = 137.6 V/m$

Date/Time: 24/10/2008 11:14:24 AM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_AM80%_900_PMF_iDEN.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: AM 80%; Frequency: 900 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 62.1 V/m; Power Drift = 0.032 dB Maximum value of Total (measured) = 86.2 V/m

RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 27(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 86.7 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 62.1 V/m; Power Drift = 0.032 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
86.1 M4	86.7 M4	83.9 M4
Grid 4	Grid 5	Grid 6
42.9 M4	44.5 M4	44.1 M4

Peak E-field in V/m $% \left({{E_{\rm{T}}}} \right) = {{E_{\rm{T}}}} \left({{E_{\rm{T}}}} \right) = {E_{\rm{T}}} \left({E_{\rm{T}}} \right) = {E_{\rm{T}}}$

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 28(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N



 $0 \ dB = 86.7 \ V/m$

Date/Time: 24/10/2008 10:57:51 AM

Test Laboratory: RTS

File Name: <u>HAC_E_Dipole_900_iDEN_PMF.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: IDEN 900; Frequency: 900 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 31.2 V/m; Power Drift = 0.084 dB Maximum value of Total (measured) = 45.2 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 30(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 45.5 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 31.2 V/m; Power Drift = 0.084 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
43.9 M4	45.5 M4	45.2 M4
Grid 4	Grid 5	Grid 6
21.6 M4	22.3 M4	22.0 M4

Peak E-field in V/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 31(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N



 $0 \; dB = 45.5 V/m$

Date/Time: 24/10/2008 11:58:51 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW835_20dBm.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.461 A/m; Power Drift = 0.064 dB Maximum value of Total (measured) = 0.435 A/m

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.436 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.461 A/m; Power Drift = 0.064 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m				
Grid 1	Grid 2	Grid 3		
0.358 M4	0.379 M4	0.370 M4		
Grid 4	Grid 5	Grid 6		
0.408 M4	0.436 M4	0.422 M4		
Grid 7	Grid 8	Grid 9		

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 34(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N



 $0 \; dB = 0.436 A/m$

Date/Time: 24/10/2008 12:06:21 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW835_PMF_iDEN.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.499 A/m; Power Drift = 0.052 dB Maximum value of Total (measured) = 0.474 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 36(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.476 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.499 A/m; Power Drift = 0.052 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)
RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 37(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N

Peak H-field i	in A/m
----------------	--------

Grid 1	Grid 2	Grid 3
0.390 M4	0.416 M4	0.405 M4
Grid 4	Grid 5	Grid 6
0.444 M4	0.476 M4	0.465 M4
Grid 7	Crid 8	Grid 0



 $0 \ dB = 0.476 \text{A/m}$

Date/Time: 24/10/2008 12:13:15 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_AM80%_835_PMF_iDEN.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: AM80%; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.324 A/m; Power Drift = -0.004 dB Maximum value of Total (measured) = 0.304 A/m

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.305 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.324 A/m; Power Drift = -0.004 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.250 M4	0.264 M4	0.258 M4
Grid 4	Grid 5	Grid 6
0.285 M4	0.305 M4	0.297 M4
Grid 7	Grid 8	Grid 9

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RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 40(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N



 $0 \ dB = 0.305 A/m$

Date/Time: 24/10/2008 12:24:56 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_835_iDEN_PMF.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: IDEN ; Frequency: 835 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.159 A/m; Power Drift = 0.228 dB Maximum value of Total (measured) = 0.153 A/m

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.154 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.159 A/m; Power Drift = 0.228 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.126 M4	0.135 M4	0.132 M4
Grid 4	Grid 5	Grid 6
0.144 M4	0.154 M4	0.150 M4
Grid 7	Grid 8	Grid 9

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RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 43(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N



 $0 \ dB = 0.154 A/m$

Date/Time: 24/10/2008 11:37:58 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW900_20dBm.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 900 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.413 A/m; Power Drift = 0.083 dB Maximum value of Total (measured) = 0.394 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model RC	ns Test CD21IN	Page 45(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.395 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.413 A/m; Power Drift = 0.083 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

	A/m	
Grid 1	Grid 2	Grid 3
0.349 M4	0.372 M4	0.363 M4
Grid 4	Grid 5	Grid 6
0.369 M4	0.395 M4	0.387 M4

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RTS RIM Testing Services	Document Annex A to Hearing Aic Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 46(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N



 $0 \ dB = 0.395 A/m$

Date/Time: 24/10/2008 11:44:58 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_CW900_PMF_iDENda4.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 900 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.426 A/m; Power Drift = 0.021 dB Maximum value of Total (measured) = 0.408 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 48(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.409 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.426 A/m; Power Drift = 0.021 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

	A/III	
Grid 1	Grid 2	Grid 3
0.366 M4	0.388 M4	0.377 M4
Grid 4	Grid 5	Grid 6
0.386 M4	0.409 M4	0.400 M4

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RTS RIM Testing Services	Document Annex A to Hearing Aic Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 49(108)	
Author Data	Dates of Test Report No FCC ID				
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N	



 $0 \ dB = 0.409 A/m$

Date/Time: 24/10/2008 11:51:45 AM

Test Laboratory: RTS

File Name: <u>HAC_H_Dipole_AM80%_900_PMF_iDENda4.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: AM_80%; Frequency: 900 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.275 A/m; Power Drift = 0.017 dB Maximum value of Total (measured) = 0.260 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 51(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	N		

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.261 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.275 A/m; Power Drift = 0.017 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.233 M4	0.248 M4	0.241 M4
Grid 4	Grid 5	Grid 6
0.245 M4	0.261 M4	0.256 M4

Peak H-field in A/m

RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ons Test CD21IN	Page 52(108)		
Author Data	Dates of Test Report No FCC ID					
Daoud Attayi	June 25, Oct 23-24, 2008	une 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN				



 $0 \ dB = 0.261 \ A/m$

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Date/Time: 24/10/2008 12:34:14 PM

Test Laboratory: RTS

File Name: HAC_H_Dipole_900_iDEN_PMF.da4

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: IDEN 900; Frequency: 900 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.144 A/m; Power Drift = 0.000 dB Maximum value of Total (measured) = 0.138 A/m

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.139 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.144 A/m; Power Drift = 0.000 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 55(108)	
Author Data	Dates of Test Report No FCC ID				
Daoud Attayi	June 25, Oct 23-24, 2008	N			

Peak H-field i	in A/m
----------------	--------

Grid 1	Grid 2	Grid 3
0.120 M4	0.130 M4	0.126 M4
Grid 4	Grid 5	Grid 6
0.128 M4	0.139 M4	0.136 M4
Grid 7	Grid 8	Grid 9



RTS RIM Testing Services	Document Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ons Test CD21IN	Page 56(108)		
Author Data	Dates of Test					
Daoud Attayi	June 25, Oct 23-24, 2008	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN				

Justification of Step Size and Interpolation

This section demonstrates that a 5mm step size with interpolation provides sufficient resolution for RF emissions measurements. The DASY 4 uses interpolation algorithms to derive 9 interpolated points between every measured point.



The figure above shows the raw measured field strength perpendicular to the length of the validation dipole. The TCB guidance slides require the 3dB width to be much larger than the step size. The width between -3dB points is ≥ 21 mm, at least 4 times the step size.



This figure shows the interpolated field strength perpendicular to the dipole. The interpolated points follow the raw points with no inconsistencies.

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RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN				
Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayl	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN		
	X-Axis is perpendicular to	~			

The green line in this figure shows the axis along which the points lie.

length of dipole

Comparison of 5mm and 2mm step sizes

An additional set of measurements was taken: dipole validations were performed using 5mm and 2mm step sizes. The delta between the two readings is insignificant for both field types (< 0.4% for E and 0% for H), demonstrating that 5mm is sufficient. The plots follow.

Date/Time: 14/07/2005 11:35:24 AM

Page 1 of 2

Date/Time: 14/07/2005 11:35:24 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m³ Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of Total (measured) = 134.8 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Maximum value of Total field (slot averaged) = 131.0 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
123.2	138.1	138.4	123.2	138.1	138.4
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
80.9	92.3	92.2	80.9	92.3	92.2
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
119.8	131.0	130.7	 119.8	131.0	130.7

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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RTS RIM Testing Services	Document Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN				
Author Data	Dates of Test	Report No	FCC ID		
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN				
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Page 2 of 2

Date/Time: 14/07/2005 11:35:24 AM



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Page 1 of 2

Date/Time: 14/07/2005 11:44:51 AM

Lab: RIM Testing Services (RTS)

Dipole Validation 1880 MHz_2mm step_E-Field 07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1000$ kg/m³ Phantom section: H Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1): Measurement grid: dx=2mm, dy=2mm

Maximum value of Total (measured) = 138.0 V/m

E Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1): Measurement grid: dx=2mm, dy=2mm Maximum value of Total field (slot averaged) = 131.2 V/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

E in V/m (Time averaged) E in V/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
123.1	138.6	138.6	123.1	138.6	138.6
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
81.4	92.1	91.6	81.4	92.1	91.6
81.4 Grid 7	92.1 Grid 8	91.6 Grid 9	81.4 Grid 7	92.1 Grid 8	91.6 Grid 9

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
М3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ons Test CD21IN	Page 61(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	Ν

Date/Time: 14/07/2005 11:44:51 AM

Page 2 of 2



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Date/Time: 14/07/2005 12:43:02 PM

Page 1 of 2

Date/Time: 14/07/2005 12:43:02 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_5 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m³ Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 SN6105; ; Calibrated: 10/12/2004
- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)
- Electronics: DAE3 Sn472; Calibrated: 03/01/2005
- Phantom: HAC Test Arch; Type: SD HAC P01 BA;
- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (5x19x1): Measurement grid: dx=5mm, dy=5mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (41x181x1): Measurement grid: dx=5mm, dy=5mm Maximum value of Total field (slot averaged) = 0.406 A/m Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
0.342	0.359	0.344	0.342	0.359	0.344
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
0.389	0.406	0.389	0.389	0.406	0.389
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
0.363	0.378	0.363	0.363	0.378	0.363

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

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RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 63(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N

Date/Time: 14/07/2005 12:43:02 PM

Page 2 of 2



file://C:\Program%20Files\DASY4\Print_Templates\HAC_H_Dipole_CW%201880_5%... 14/07/2005

Date/Time: 14/07/2005 12:53:40 PM

Page 1 of 2

Date/Time: 14/07/2005 12:53:40 PM

Lab: RIM Testing Services (RTS)

HAC_H_Dipole_CW 1880_2 mm step_07_14_05

DUT: HAC Dipole 1880 MHz; Type: CD1880V3

Communication System: CW; Frequency: 1880 MHz;Duty Cycle: 1:1 Medium: Air Medium parameters used: $\sigma = 0$ mho/m, $\varepsilon_r = 1$; $\rho = 1$ kg/m³ Phantom section: H Dipole Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 10/12/2004

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 03/01/2005

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.5 Build 19; Postprocessing SW: SEMCAD, V1.8 Build 146

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (11x46x1): Measurement grid: dx=2mm, dy=2mm

Maximum value of Total (measured) = 0.406 A/m

H Scan 10mm above CD 1880 MHz/Hearing Aid Compatibility Test (101x451x1):

Measurement grid: dx=2mm, dy=2mm Maximum value of Total field (slot averaged) = 0.406 A/m

Hearing Aid Near-Field Category: M2 (AWF 0 dB)

H in A/m (Time averaged) H in A/m (Slot averaged)

Grid 1	Grid 2	Grid 3	Grid 1	Grid 2	Grid 3
0.347	0.361	0.348	0.347	0.361	0.348
Grid 4	Grid 5	Grid 6	Grid 4	Grid 5	Grid 6
0.394	0.406	0.391	0.394	0.406	0.391
Grid 7	Grid 8	Grid 9	Grid 7	Grid 8	Grid 9
0.367	0.380	0.365	0.367	0.380	0.365

Category	AWF (dB)	Limits for E-Field Emissions (V/m)	Limits for H-Field Emissions (A/m)
M1	0	199.5 - 354.8	0.6 - 1.07
	-5	149.6 - 266.1	0.45 - 0.8
M2	0	112.2 - 199.5	0.34 - 0.6
	-5	84.1 - 149.6	0.25 - 0.45
M3	0	63.1 - 112.2	0.19 - 0.34
	-5	47.3 - 84.1	0.15 - 0.25
M4	0	<63.1	<0.19

file://C:\Program%20Files\DASY4\Print_Templates\HAC_H_Dipole_CW%201880_2%... 14/07/2005

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ons Test CD21IN	Page 65(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N

Date/Time: 14/07/2005 12:53:40 PM

Page 2 of 2



file://C:\Program%20Files\DASY4\Print_Templates\HAC_H_Dipole_CW%201880_2%... 14/07/2005

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RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ons Test CD21IN	Page 66(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N

A.3 RF emissions and ambient noise data/plots

Date/Time: 24/10/2008 2:48:21 PM

Test Laboratory: RTS

File Name: HAC_E_iDEN800_Low_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: IDEN ; Frequency: 806.013 MHz;Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 79.1 V/m; Power Drift = -0.211 dB

Maximum value of Total (measured) = 67.8 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid:

dx=5mm, dy=5mm

Maximum value of peak Total field = 225.6 V/m

Probe Modulation Factor = 3.33

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 79.1 V/m; Power Drift = -0.211 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Feak E-field III	V/111	
Grid 1	Grid 2	Grid 3
212.1 M3	226.1 M3	223.1 M3
Grid 4	Grid 5	Grid 6
201.8 M3	225.6 M3	223.4 M3
Grid 7	Grid 8	Grid 9

Peak E-field in V/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 69(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N



Date/Time: 24/10/2008 2:59:52 PM

Test Laboratory: RTS

File Name: <u>HAC_E_iDEN800_Mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: IDEN ; Frequency: 813.5 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 72.5 V/m; Power Drift = -0.028 dB

Maximum value of Total (measured) = 62.9 V/m

E Scan - ER3D - 2007: 15 mm from Probe Center to the

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

Device/Hearing Aid Compatibility Test (101x101x1): Measurement grid:

dx=5mm, dy=5mm

Maximum value of peak Total field = 208.8 V/m

Probe Modulation Factor = 3.33

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 72.5 V/m; Power Drift = -0.028 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Grid 1	Grid 2	Grid 3			
195.2 M4	209.7 M3	203.6 M3			
Grid 4	Grid 5	Grid 6			
189.3 M4	208.8 M3	204.4 M3			

Peak E-field in V/m

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	Page 72(108)		
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	


Date/Time: 24/10/2008 3:10:16 PM

Test Laboratory: RTS

File Name: <u>HAC_E_iDEN800_High_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: IDEN ; Frequency: 824.987 MHz;Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 73.9 V/m; Power Drift = 0.227 dB

Maximum value of Total (measured) = 64.1 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N

dx=5mm, dy=5mm

Maximum value of peak Total field = 213.6 V/m

Probe Modulation Factor = 3.33

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 73.9 V/m; Power Drift = 0.227 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
202.8 M3	213.7 M3	210.1 M3
Grid 4	Grid 5	Grid 6
198.8 M4	213.6 M3	212.3 M3
Grid 7	Grid 8	Grid 9



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N

Date/Time: 24/10/2008 3:20:01 PM

Test Laboratory: RTS

File Name: <u>HAC_E_iDEN900_Low_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: IDEN 900; Frequency: 896 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 100.4 V/m; Power Drift = -0.021 dB

Maximum value of Total (measured) = 84.0 V/m

RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 77(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N

dx=5mm, dy=5mm

Maximum value of peak Total field = 253.6 V/m

Probe Modulation Factor = 3.02

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 100.4 V/m; Power Drift = -0.021 dB

Hearing Aid Near-Field Category: M3 (AWF 0 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
239.5 M3	254.1 M3	251.7 M3
Grid 4	Grid 5	Grid 6
228.5 M3	253.6 M3	251.3 M3
Grid 7	Grid 8	Grid 9



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N

Date/Time: 24/10/2008 3:28:32 PM

Test Laboratory: RTS

File Name: <u>HAC_E_iDEN900_Mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: IDEN 900; Frequency: 898.5 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 73.4 V/m; Power Drift = 0.066 dB

Maximum value of Total (measured) = 65.3 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N

dx=5mm, dy=5mm

Maximum value of peak Total field = 195.9 V/m

Probe Modulation Factor = 3.02

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 73.4 V/m; Power Drift = 0.066 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
187.9 M4	198.6 M4	198.6 M4
Grid 4	Grid 5	Grid 6
172.7 M4	195.9 M4	195.9 M4
Grid 7	Grid 8	
155.9 M4	179.3 M4	Grid 9



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N

 $0 \ dB = 198.5 V/m$

Date/Time: 24/10/2008 3:37:13 PM

Test Laboratory: RTS

File Name: HAC_E_iDEN900_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF ER3D Device

Communication System: IDEN 900; Frequency: 901 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1000$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2285; ConvF(1, 1, 1); Calibrated: 07/03/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - ER3D - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 73.8 V/m; Power Drift = -0.227 dB

Maximum value of Total (measured) = 62.1 V/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 83(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008 RTS-1271-0810-32 L6ARCD20IN			N

dx=5mm, dy=5mm

Maximum value of peak Total field = 187.4 V/m

Probe Modulation Factor = 3.02

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 73.8 V/m; Power Drift = -0.227 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak E-field in	V/m	
Grid 1	Grid 2	Grid 3
179.4 M4	187.6 M4	186.7 M4
Grid 4	Grid 5	Grid 6
168.9 M4	187.4 M4	187.3 M4
Grid 7	Grid 8	Grid 9



RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 84(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N

Date/Time: 24/10/2008 4:22:42 PM

Test Laboratory: RTS

File Name: <u>HAC_H_iDEN800_Low_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: IDEN 800; Frequency: 806.013 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.093 A/m; Power Drift = -0.024 dB

Maximum value of Total (measured) = 0.153 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN		Page 86(108)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.454 A/m

Probe Modulation Factor = 3.09

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.093 A/m; Power Drift = -0.024 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.472 M4	0.346 M4	0.230 M4
Grid 4	Grid 5	Grid 6
0.451 M4	0.344 M4	0.222 M4
Grid 7	Grid 8	Grid 9



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN		Page 87(108)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N

Date/Time: 24/10/2008 4:30:44 PM

Test Laboratory: RTS

File Name: <u>HAC_H_iDEN800_Mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: IDEN 800; Frequency: 813.5 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.096 A/m; Power Drift = -0.165 dB

Maximum value of Total (measured) = 0.167 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN		Page 89(108)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.517 A/m

Probe Modulation Factor = 3.09

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.096 A/m; Power Drift = -0.165 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m
Grid 1	Gr

Grid 1	Grid 2	Grid 3
0.471 M4	0.348 M4	0.222 M4
Grid 4	Grid 5	Grid 6
0.495 M4	0.360 M4	0.226 M4



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN		Page 90(108)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N

Date/Time: 24/10/2008 4:38:25 PM

Test Laboratory: RTS

File Name: HAC_H_iDEN800_High_Chan.da4

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: IDEN 800; Frequency: 824.987 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.089 A/m; Power Drift = -0.122 dB

Maximum value of Total (measured) = 0.154 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN		Page 92(108)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.476 A/m

Probe Modulation Factor = 3.09

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.089 A/m; Power Drift = -0.122 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.473 M4	0.337 M4	0.215 M4
Grid 4	Grid 5	Grid 6
0.468 M4	0.334 M4	0.206 M4



RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN		Page 93(108)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	N

Date/Time: 24/10/2008 4:14:09 PM

Test Laboratory: RTS

File Name: <u>HAC_H_iDEN900_Low_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: IDEN 900; Frequency: 896 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.114 A/m; Power Drift = -0.194 dB

Maximum value of Total (measured) = 0.186 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN		Page 95(108)	
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.546 A/m

Probe Modulation Factor = 2.94

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.114 A/m; Power Drift = -0.194 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in	A/m	
Grid 1	Grid 2	Grid 3
0.529 M4	0.388 M4	0.249 M4
Grid 4	Grid 5	Grid 6
0.522 M4	0.391 M4	0.256 M4
Grid 7	Grid 8	Grid 9



RTS RIM Testing Services	Document Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 96(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N

Date/Time: 24/10/2008 4:06:10 PM

Test Laboratory: RTS

File Name: <u>HAC_H_iDEN900_Mid_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: IDEN 900; Frequency: 898.5 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.117 A/m; Power Drift = 0.178 dB

Maximum value of Total (measured) = 0.182 A/m

RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 98(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.536 A/m

Probe Modulation Factor = 2.94

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.117 A/m; Power Drift = 0.178 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Peak H-field in A/m	

Grid 1	Grid 2	Grid 3
0.521 M4	0.396 M4	0.270 M4
Grid 4	Grid 5	Grid 6
0.525 M4	0.403 M4	0.278 M4
Grid 7	Grid 8	Grid 9



RTS RIM Testing Services	Document Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 99(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20II	N

Date/Time: 24/10/2008 3:52:19 PM

Test Laboratory: RTS

File Name: <u>HAC_H_iDEN900_High_Chan.da4</u>

DUT: BlackBerry Smartphone; Type: Sample ; Serial: Not Specified Program Name: HAC RF H3DV6 Device

Communication System: IDEN 900; Frequency: 901 MHz; Duty Cycle: 1:3

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; $\rho = 1$ kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - H3DV6 - 2007: 15 mm from Probe Center to the

Device/Hearing Aid Compatibility Test (11x11x1): Measurement grid:

dx=5mm, dy=5mm

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.100 A/m; Power Drift = -0.083 dB

Maximum value of Total (measured) = 0.160 A/m

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 101(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

dx=5mm, dy=5mm

Maximum value of peak Total field = 0.453 A/m

Probe Modulation Factor = 2.94

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.100 A/m; Power Drift = -0.083 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1 Grid 2 Grid 3 **0.470 M4** 0.237 M4 0.353 M4 Grid 4 Grid 5 Grid 6 0.455 M4 0.342 M4 0.231 M4 Grid 7 Grid 8 Grid 9 0.337 M4 0.453 M4 0.227 M4



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Peak H-field in A/m

RTS RIM Testing Services	Annex A to Hearing Aic Report for the BlackBe	I Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 102(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

 $0 \; dB = 0.470 A/m$

Date/Time: 25/06/2008 10:44:08

AM

Test Laboratory: RTS

File Name: <u>HAC_E_Ambient Noise_835MHz.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF E Dipole

Communication System: CW; Frequency: 835 MHz;Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; density = 1000 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: ER3DV6 - SN2286; ConvF(1, 1, 1); Calibrated: 21/01/2008

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

E Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.000 V/m; Power Drift = 999.0 dB Maximum value of Total (measured) = 1.68 V/m

E Scan - measurement distance from the probe sensor center to

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 104(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 1.68 V/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.000 V/m; Power Drift = 999.0 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
1.57 M4	0.408 M4	0.000 M4
Grid 4	Grid 5	Grid 6
1.59 M4	1.18 M4	1.68 M4
1.59 M4 Grid 7	1.18 M4 Grid 8	1.68 M4 Grid 9

Peak E-field in V/m

RTS RIM Testing Services	Document Annex A to Hearing Aic Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ons Test CD21IN	Page 105(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20I	Ν



 $0 \ dB = 1.68 V/m$

Date/Time: 25/06/2008 2:32:22 PM

Test Laboratory: RTS

File Name: <u>HAC_H_Ambient Noise_835MHz.da4</u>

DUT: HAC-Dipole 835 MHz; Type: D835V3; Serial: Not Specified Program Name: HAC RF H3DV6 Dipole

Communication System: CW; Frequency: 835 MHz; Duty Cycle: 1:1

Medium parameters used: $\sigma = 0$ mho/m, $\epsilon_r = 1$; density = 1 kg/m³

Phantom section: E Device Section

DASY4 Configuration:

- Probe: H3DV6 - SN6105; ; Calibrated: 09/11/2007

- Sensor-Surface: 0mm (Fix Surface)Sensor-Surface: (Fix Surface)

- Electronics: DAE3 Sn472; Calibrated: 05/03/2008

- Phantom: HAC Test Arch; Type: SD HAC P01 BA;

- Measurement SW: DASY4, V4.7 Build 71; Postprocessing SW: SEMCAD, V1.8 Build 184

H Scan - measurement distance from the probe sensor center to CD835 Dipole = 10mm/Hearing Aid Compatibility Test (5x37x1): Measurement grid: dx=5mm, dy=5mm Probe Modulation Factor = 1.00 Device Reference Point: 0.000, 0.000, 353.7 mm Reference Value = 0.003 A/m; Power Drift = 1.02 dB Maximum value of Total (measured) = 0.007 A/m

H Scan - measurement distance from the probe sensor center to

RTS RIM Testing Services	Annex A to Hearing Aid Report for the BlackBe	l Compatibility RF Emissio rry® Smartphone model R0	ns Test CD21IN	Page 107(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	N

CD835 Dipole = 10mm/Hearing Aid Compatibility Test (41x361x1):

Measurement grid: dx=5mm, dy=5mm

Maximum value of peak Total field = 0.007 A/m

Probe Modulation Factor = 1.00

Device Reference Point: 0.000, 0.000, 353.7 mm

Reference Value = 0.003 A/m; Power Drift = 1.02 dB

Hearing Aid Near-Field Category: M4 (AWF 0 dB)

Grid 1	Grid 2	Grid 3
0.000 M4	0.006 M4	0.005 M4
Grid 4	Grid 5	Grid 6
0.000 M4	0.001 M4	0.002 M4
Grid 7	Grid 8	Grid 9
0.000 M4	0.003 M4	0.007 M4

Peak H-field in A/m

RTS RIM Testing Services	Annex A to Hearing Aid Compatibility RF Emissions Test Report for the BlackBerry® Smartphone model RCD21IN			Page 108(108)
Author Data	Dates of Test	Report No	FCC ID	
Daoud Attayi	June 25, Oct 23-24, 2008	RTS-1271-0810-32	L6ARCD20IN	



 $0 \ dB = 0.007 A/m$